# ASIA Hybrid Platform

Digitally Controlled IGBT Gate Driver for HVDC Applications with Advance Protection Features in a Short -Circuit Type II Scenario Richa Singh, Power Integrations GmbH

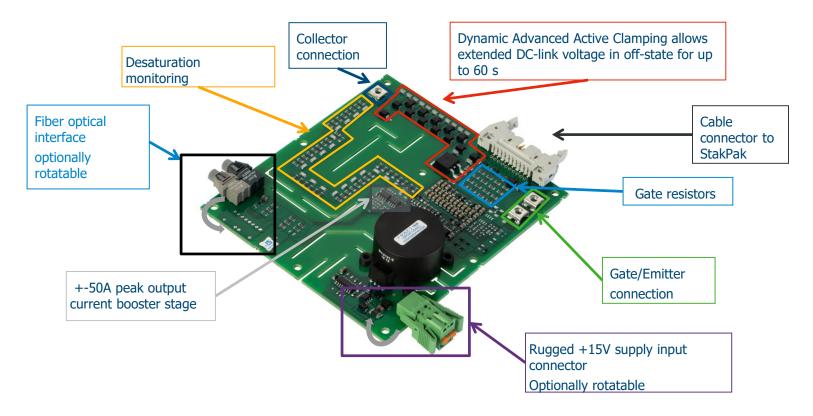
## **About the Speaker**

**Richa Singh** is an Application Engineer in Industrial Gate Driver group of Power Integrations, where I am working on Gate drivers for HVDC applications. She received her Bachelors degree from Galgotias College of Engineering and Technology, India and Masters degree from Ernst Abbe Hochschule, Jena, Germany. During her Masters internship and thesis, she worked in Robert Bosch GmbH for an year on topics related to characterization of passive components. Later she worked for 2 years in Würth Elektronik GmbH as a Product Manager for passive components.





#### **1SP0351-Functional Blocks**



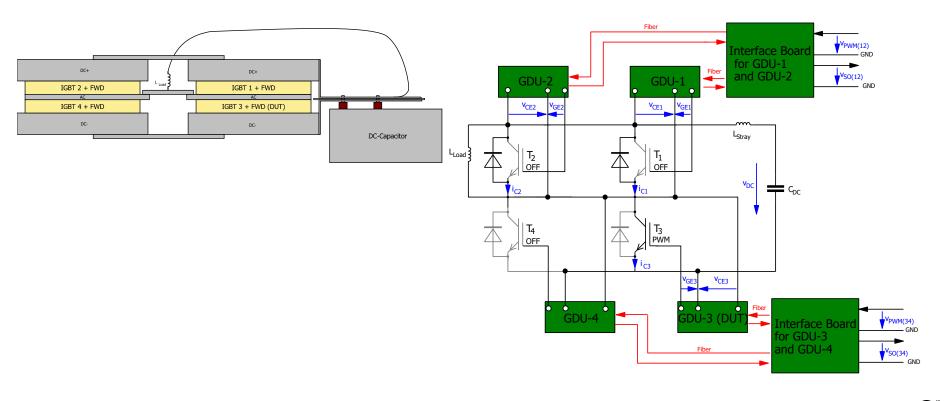
#### **Data for Press Pack IGBT used as DUT**

DC collector current (I <sub>c</sub> )	2000A
Collector-emitter voltage (V <sub>CES</sub> )	4500V
Gate-emitter voltage (V <sub>GES</sub> )	±20V
Mounting force (F <sub>M</sub> )	70kN



#### Normal IGBT Switching Characteristics

# **Normal Switching–Equivalent Circuit**

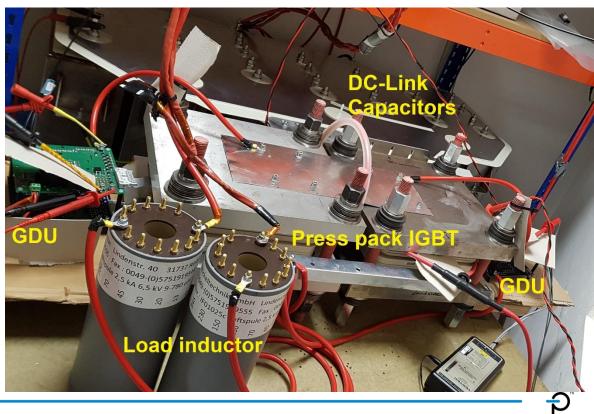


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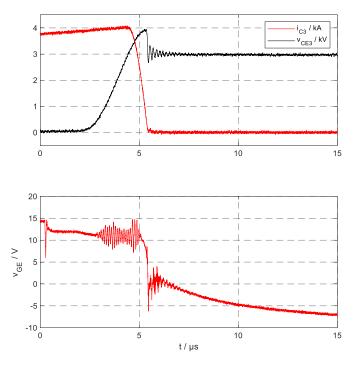
# **Normal Switching–Test Setup**

- DUT: 55NA 2000K452300
- GDU: 1SP0351
- The parallel connection is necessary in order to realize the SC condition without saturating the other IGBT



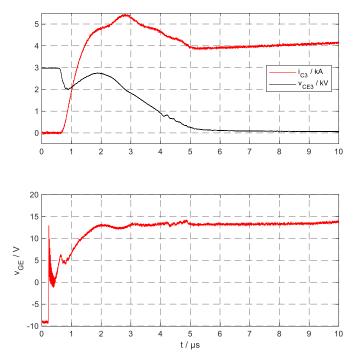
## **Normal Switching–Turn-OFF**

- Single-Pulse-Test was performed on ABB's 5SNA 2000K452300
- V<sub>DC</sub> = 3000V
- i<sub>c</sub> = 4000A



## **Normal Switching–Turn-ON**

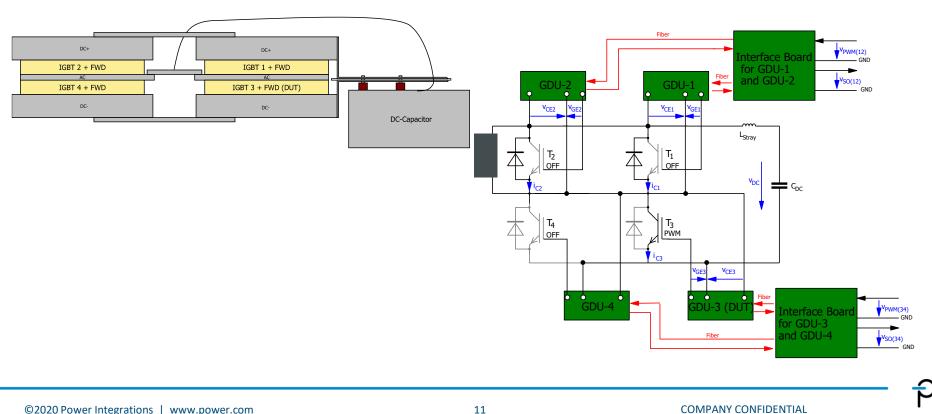
- Double-Pulse-Test was performed on ABB's 5SNA 2000K452300
- V<sub>DC</sub> = 3000V
- i<sub>c</sub> = 4000A



# **Short Circuit Type I**

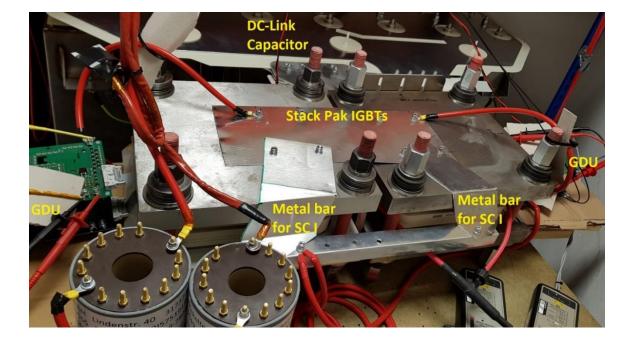
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#### **Short Circuit Type I–Equivalent Circuit**



# **Short Circuit Type I–Test Setup**

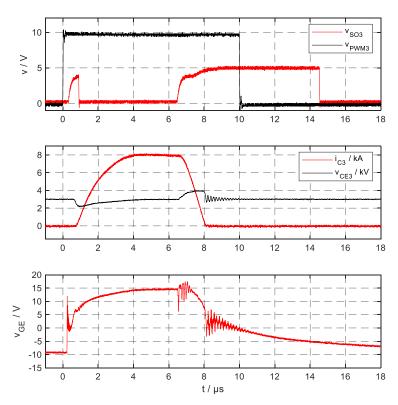
- DUT: 55NA 2000K452300
- GDU: 1SP0351
- Load inductor is replaced by metal bar





## **Short Circuit Type I–Result**

- V<sub>DC</sub> = 3000V
- i<sub>sc</sub> = 8kA

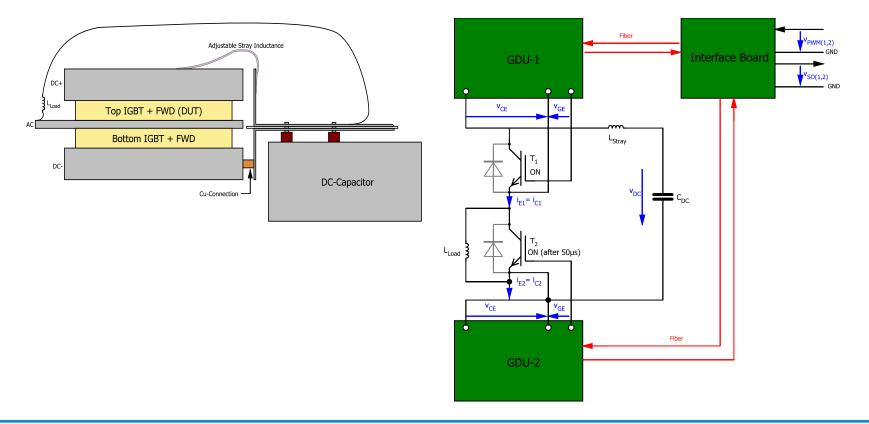


# **Bridge Shoot Through**



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## **Bridge Shoot Through–Equivalent Circuit**



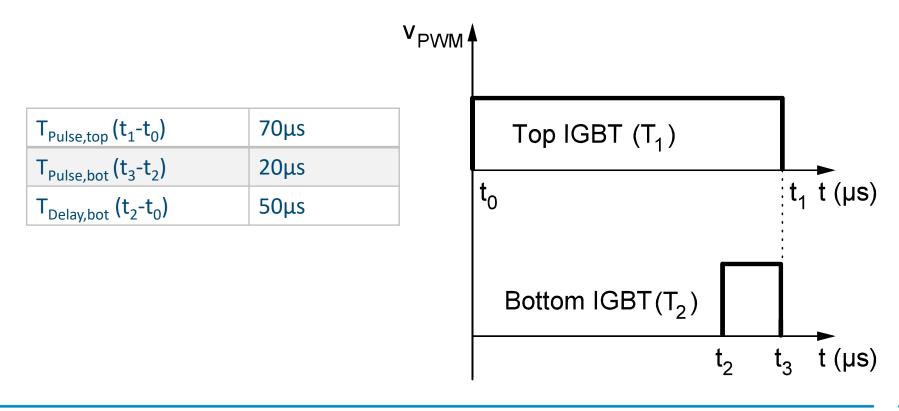
# **Bridge Shoot Through–Test Setup**

- DUT: 55NA 2000K452300
- **GDU: 1SP0351**



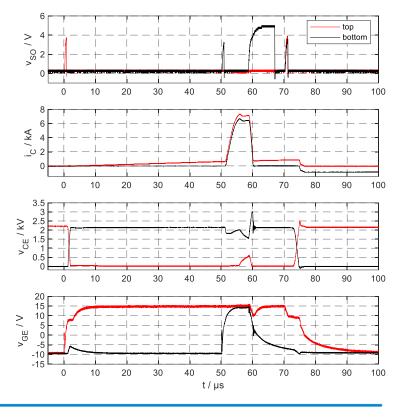


# Bridge Shoot Through–Control Signal



# **Bridge Shoot Through–Result**

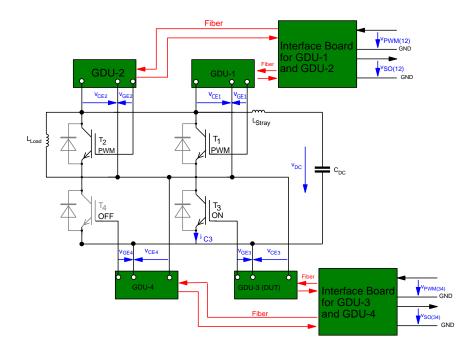
- V<sub>DC</sub> = 2200V
- i<sub>SC,top</sub> = 7.3kA i<sub>SC,bot</sub> = 6.7kA



# **Short Circuit Type II**

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# Short Circuit Type II–Equivalent Circuit

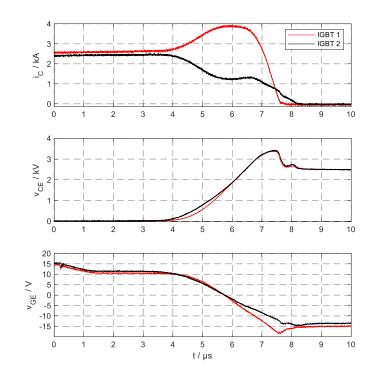


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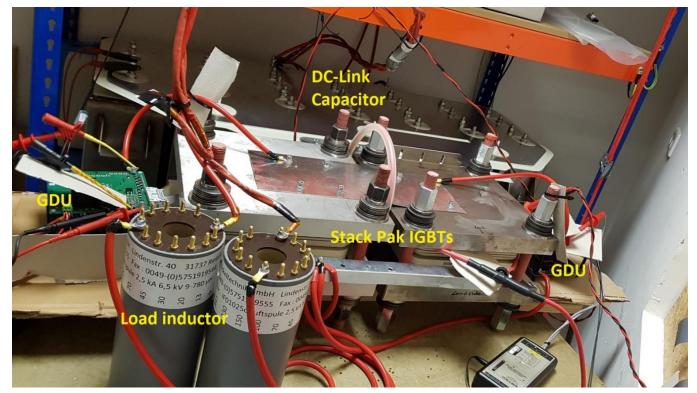
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# **Current Sharing during Turn-Off for T<sub>1</sub> and T<sub>2</sub>**

 Due to the distance differences between T<sub>1</sub> and T<sub>2</sub> to the DC link capacitor, IGBT T<sub>1</sub> (red) takes dynamically more current than IGBT T<sub>2</sub> (black), but is still sufficient for testing IGBT T<sub>3</sub> in SC II scenario. The static current sharing (t < 4 µs) is optimal.



#### **Short Circuit Type II–Test Setup**





#### **Short Circuit Type II–Control Signals**

	V <sub>PWM</sub>				
	1	Bottom IGBT (T <sub>3</sub> )		7	
60µs					
15µs		t <sub>0</sub>			t <sub>1</sub> t (µs)
40µs					
	1		Top IGBTs $(T_1 and T_2)$		
				t <sub>2</sub>	t <sub>3</sub> t (µs)

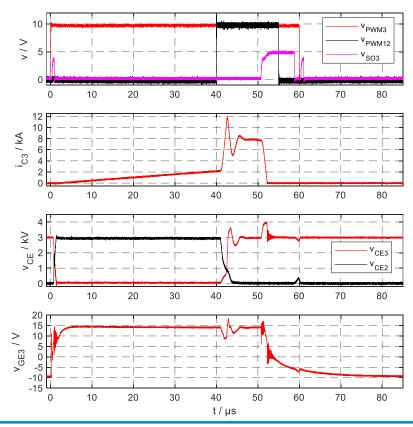
 $T_{Pulse,bot}(t_1-t_0)$ 

 $T_{Pulse,top}(t_3-t_2)$ 

 $T_{\text{Delay,bot}}(t_2-t_0)$ 

#### **Short Circuit Type II–Result**

- V<sub>DC</sub> = 3000V
- i<sub>sc3</sub> = 11.8kA



#### Conclusion

- Gate Driver function is to protect costly power semiconductor
- Power Integrations 1SP0351 gate driver can protect the IGBT in 3 different short circuit scenario – SC I, Bridge-Shoot-Through, SC II
- A fault signal is generated by the gate-driver which turns off the IGBT within the SCSOA

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#### **For Further Question**

#### Please drop an E-mail:

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